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Ionizing Radiations and Annealing Influence on MOSFET Charge States

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Abstract: The threshold voltage shift ΔV_T and its components due to trapped-oxide charges ΔV_{Not} and $Si\text{-}SiO_2$ interface traps ΔV_N in MOSFET exposed to Bremsstrahlung, Co_{60} irradiation and annealing were studied. Several effects caused by differences in the photon energies from two types of sources are discussed as well as a mechanism of changing the trapped-oxide and $Si\text{-}SiO_2$ interface traps by annealing. The mechanism is based on previously available models.

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